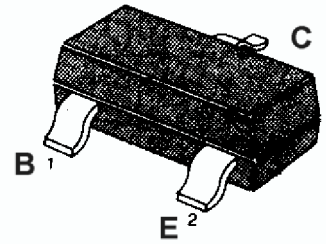


MAXIMUM RATINGS (Ta=25°C)

| PARAMETER | SYMBOL | RATING | UNIT |
|-----------------------------|------------------|---------|------|
| Collector-base voltage | V _{CBO} | 20 | V |
| Collector-emitter voltage | V _{CEO} | 8 | V |
| Emitter-base voltage | V _{EBO} | 3 | V |
| Collector current | I _C | 100 | mA |
| Collector Power Dissipation | P _C | 150 | mW |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature Range | T _{stg} | -55~150 | °C |

SOT-23



1.Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS

(Ta=25°C)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|-------------------------------------|-------------------|------|------|------|------|--|
| DC Current Gain | h _{FE} | 50 | | 300 | | V _{CE} = 3V, I _C = 10mA |
| Collector Cut-off Current | I _{CBO} | | | 1 | μA | V _{CB} = 10V, I _E =0 |
| Emitter Cut-off Current | I _{EBO} | | | 1 | μA | V _{EB} = 1V, I _C =0 |
| Collector-Base Breakdown Voltage | BV _{CBO} | 20 | | | V | I _C = 0.1mA, I _E =0 |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | 8 | | | V | I _C = 1mA, I _B =0 |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 3 | | | V | I _E = 0.1mA, I _C =0 |
| Gain bandwidth product | f _T | 3 | 7 | | GHz | I _C = 20mA, V _{CE} = 3V |
| Noise Figure | N _F | | 1.1 | | dB | V _{CE} = 3V, I _C = 10mA, f= 1GHz |

h_{FE} Classification And Marking

| | | | |
|-----------------|--------|--------|---------|
| Print Mark | R23 | R24 | R25 |
| Classification | Q | R | S |
| h _{FE} | 50~100 | 80~160 | 125~300 |